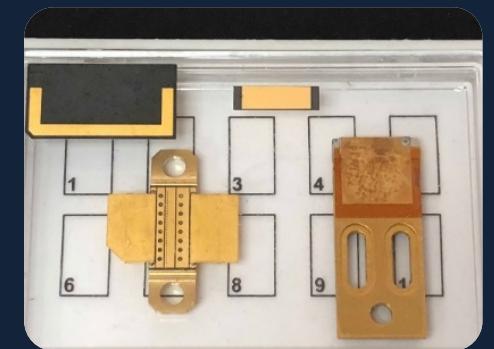


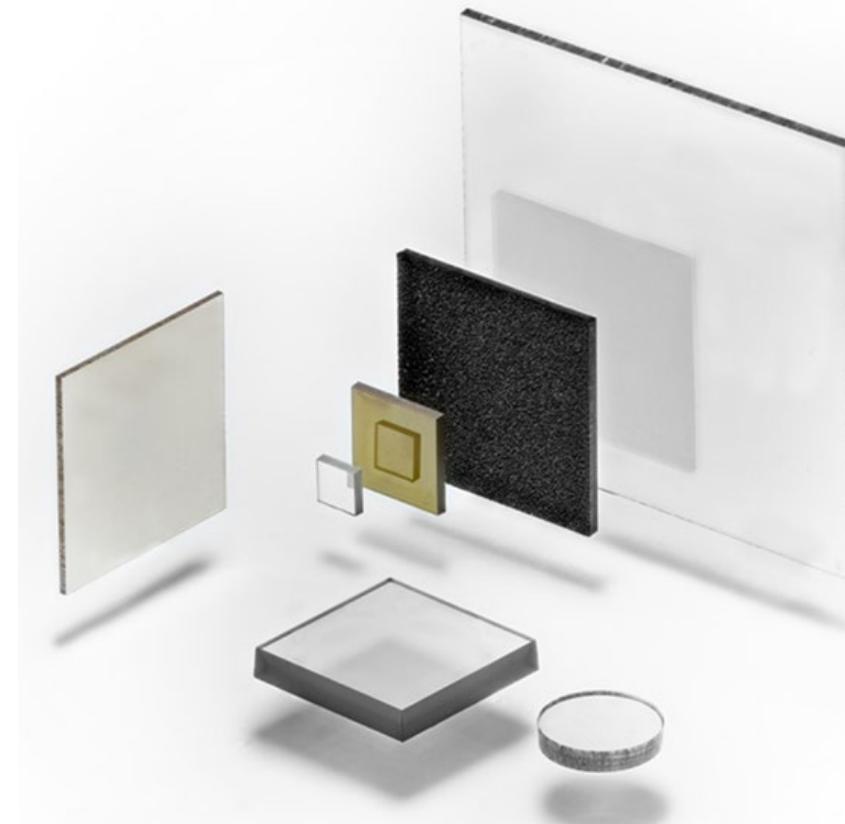
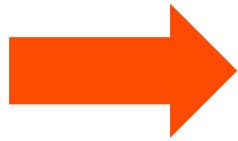
Step change thermal management of RF devices using CVD diamond

Commercially available heat spreaders



70 years of turning a natural curiosity
to an engineered material

elementsix™
DE BEERS GROUP



1. Motivation

Applications for GaN devices

Discrete HEMTs

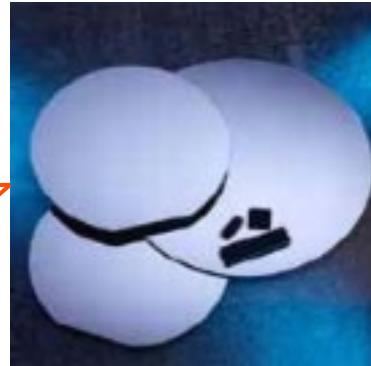


Defense Apps
(eg Radar, EW,
Avionics)



Energy-
efficient
wireless
networking

MMICs & Hybrid PAs



More efficient
Inverters for
PV/Wind

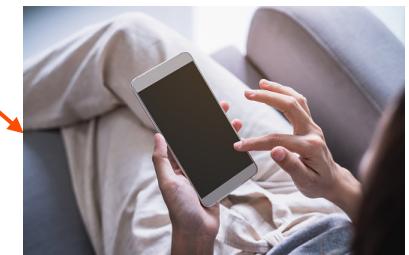


More efficient
Inverters for
Hybrids/EVs

Switches & Diodes

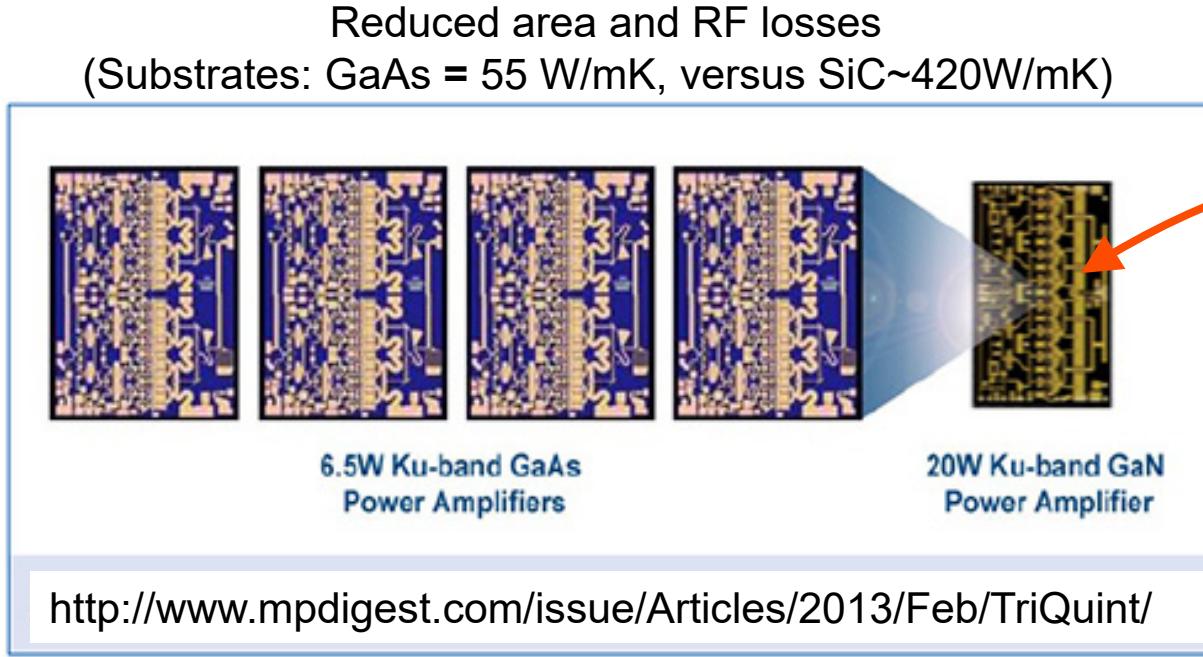


New & Efficient
Weather & Comm.
Satellites

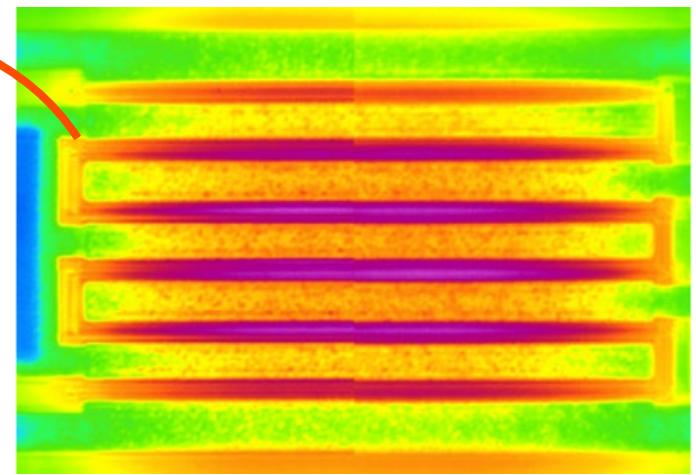


More powerful
smartphones

GaN HEMTs enable a 5x increase in RF power density w.r.t. GaAs

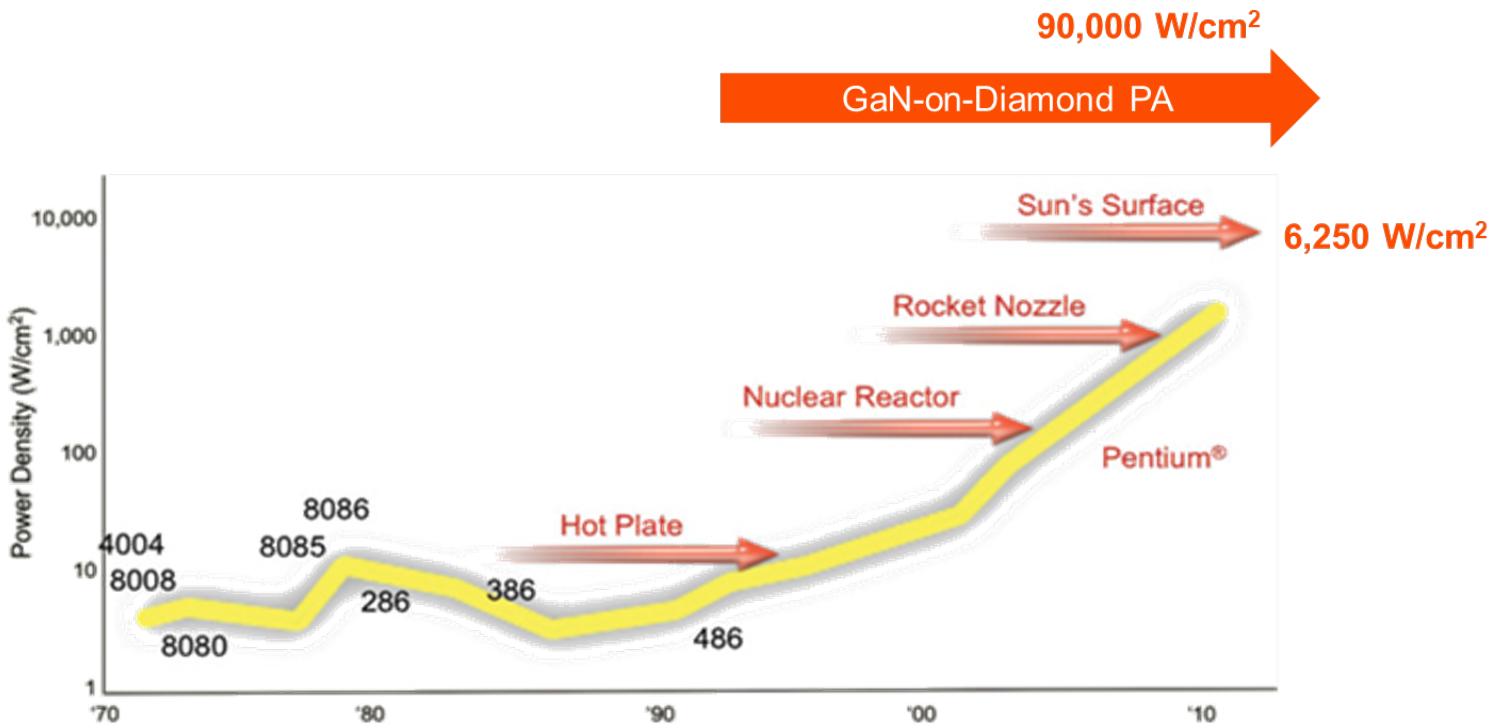


GaN-on-SiC is power density is thermally limited!

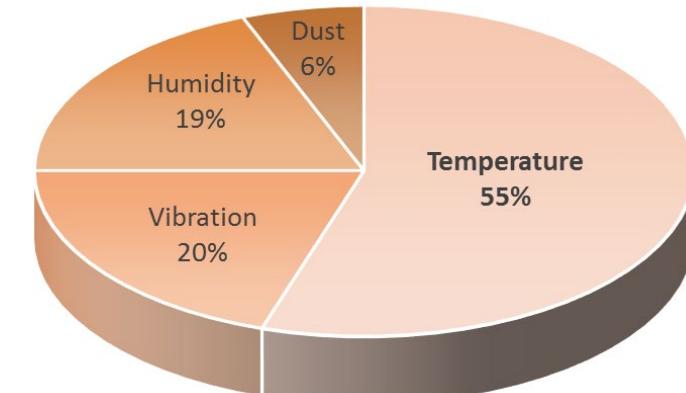


Higher power densities require improved near junction thermal transport

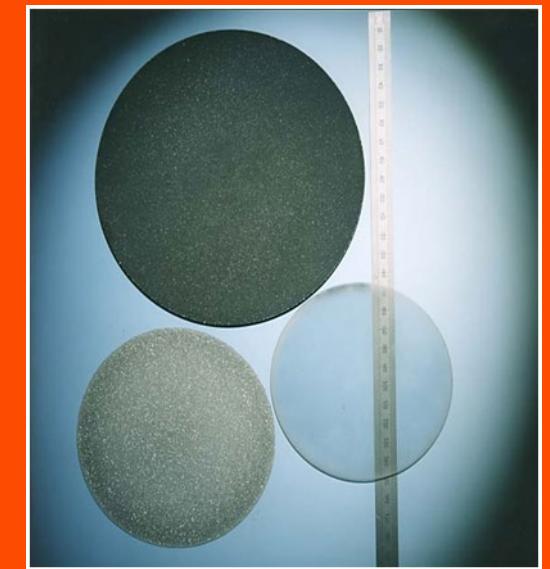
Power densities for GaN devices is rapidly increasing and temperature is a major failing mode



Failure modes in electronic systems
(Source: US Air Force)

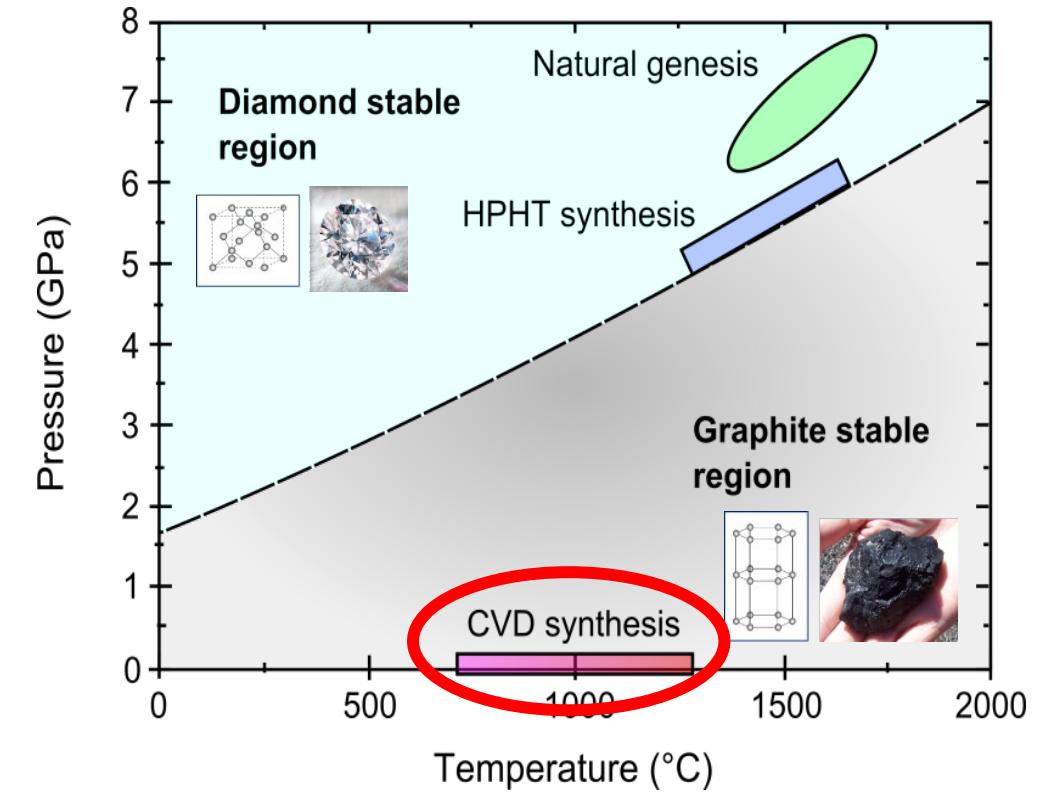
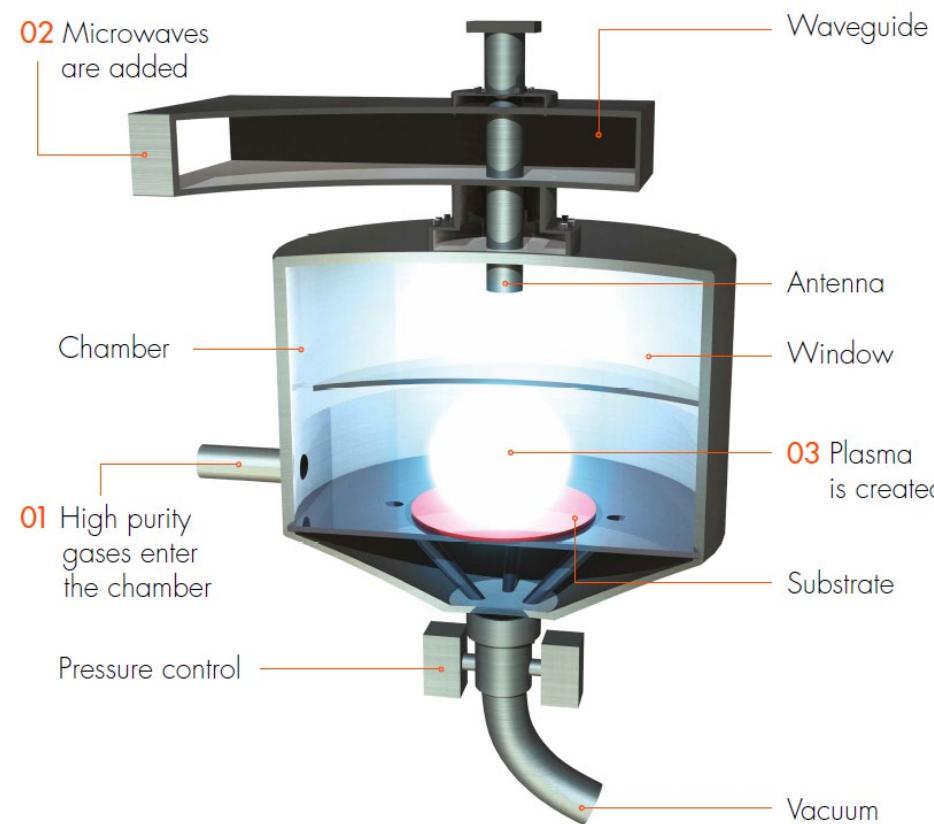


2. CVD diamond materials

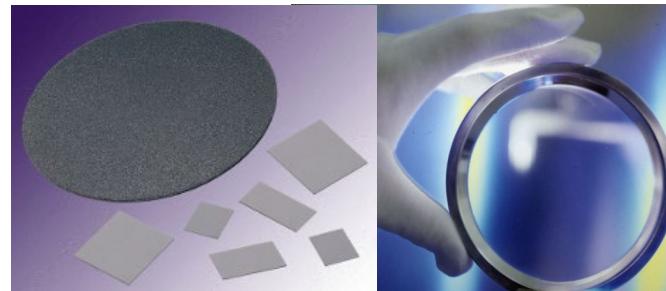
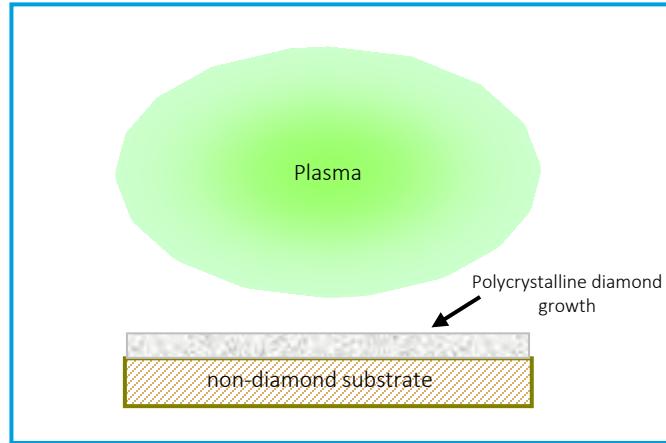


Chemical vapour deposition (CVD)

Grow under meta-stable conditions for diamond

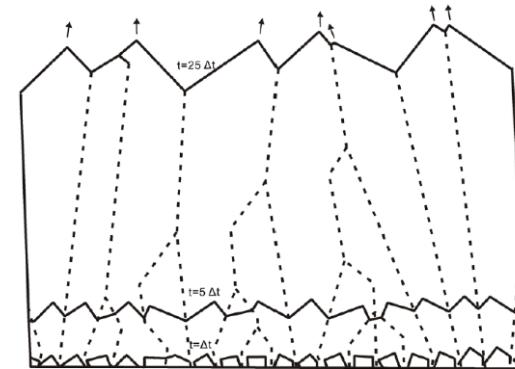


Non-diamond substrate → polycrystalline diamond growth

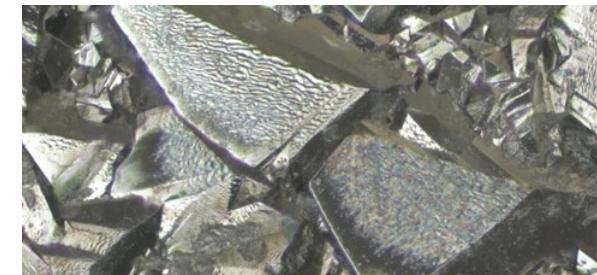


150 mm diameter & 4 mm thick

van der Drift growth model

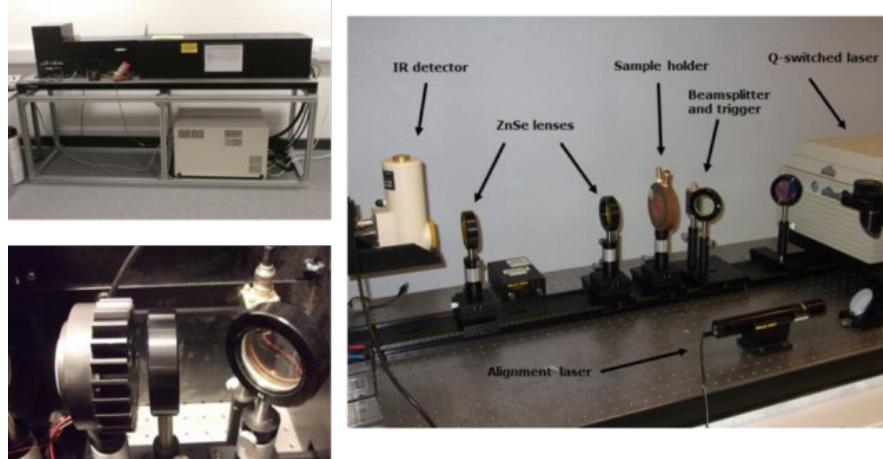


- Initial diamond nuclei are randomly oriented
 - Competitive grain growth ensues: Fastest growing grains dominate
 - Grains size ~5-10% of thickness



Measuring bulk and interface conductivity

Laser Flash for through plane bulk measurement



Heated Bar for in-plane bulk measurement

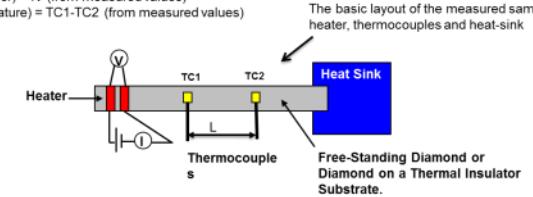
The in-plane thermal conductivity of the diamond is calculated, by using simple Joule heating thermometry [1].

1. Thermal resistance is calculated by: $R = \Delta T/\text{Power}$
2. Thermal conductivity is calculated by: $k = L/R\Delta T$

Where:

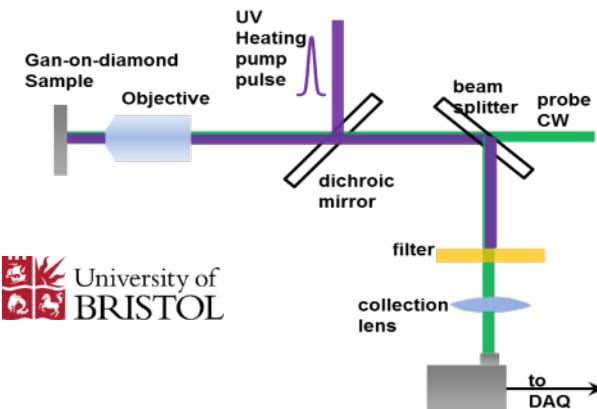
TC1 (thermocouple 1 reading): Temperature of the spot closer to heater
TC2 (thermocouple 2 reading): Temperature of the spot closer to sink
L: The fixed distance between the two thermocouple tips
A: Cross sectional area of the diamond strip
Power (dissipated power) = IV (from measured values)
 ΔT (differential temperature) = TC1-TC2 (from measured values)

The basic layout of the measured sample, heater, thermocouples and heat-sink

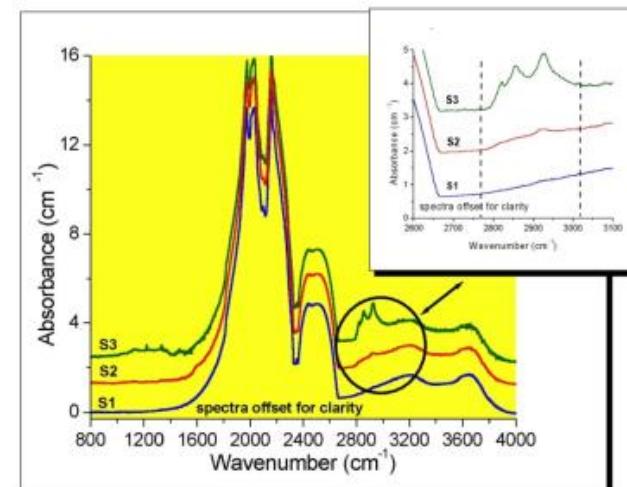


[1] S.D. Wolter *, D.-A. a. Borca-Tasciucb, G. Chenb, N. Govindarajua, R. Collazo, F. Okuzumi, J.T. Praferc, Z. Sitara, "Thermal conductivity of epitaxially textured diamond films"; * Diamond and Related Materials 12 (2003) 61-64

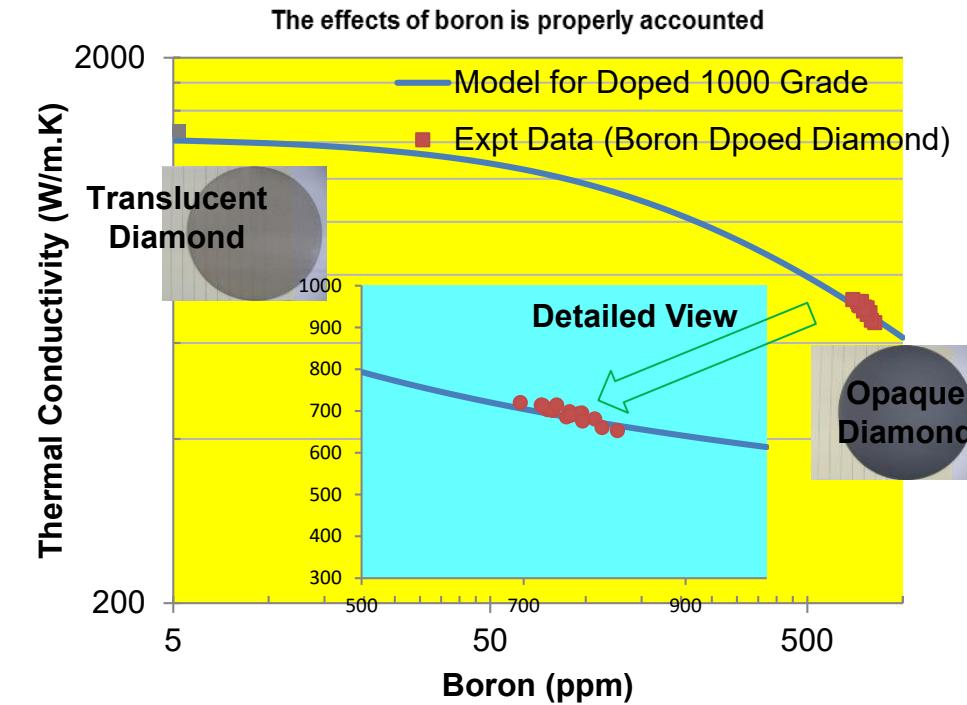
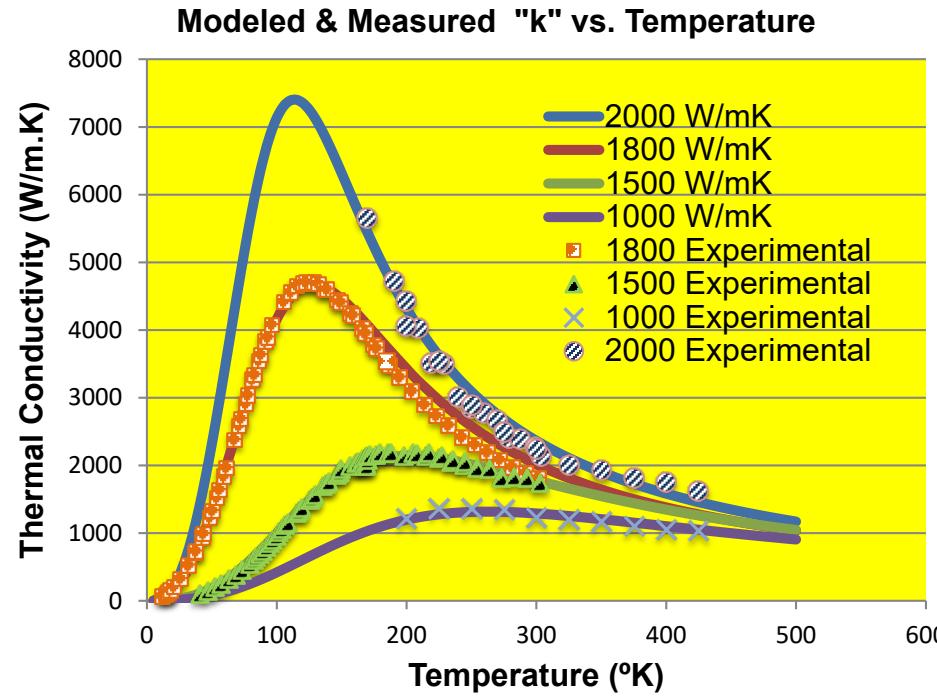
Transient thermo-reflectance technique for TBR



FTIR for through plane bulk measurement



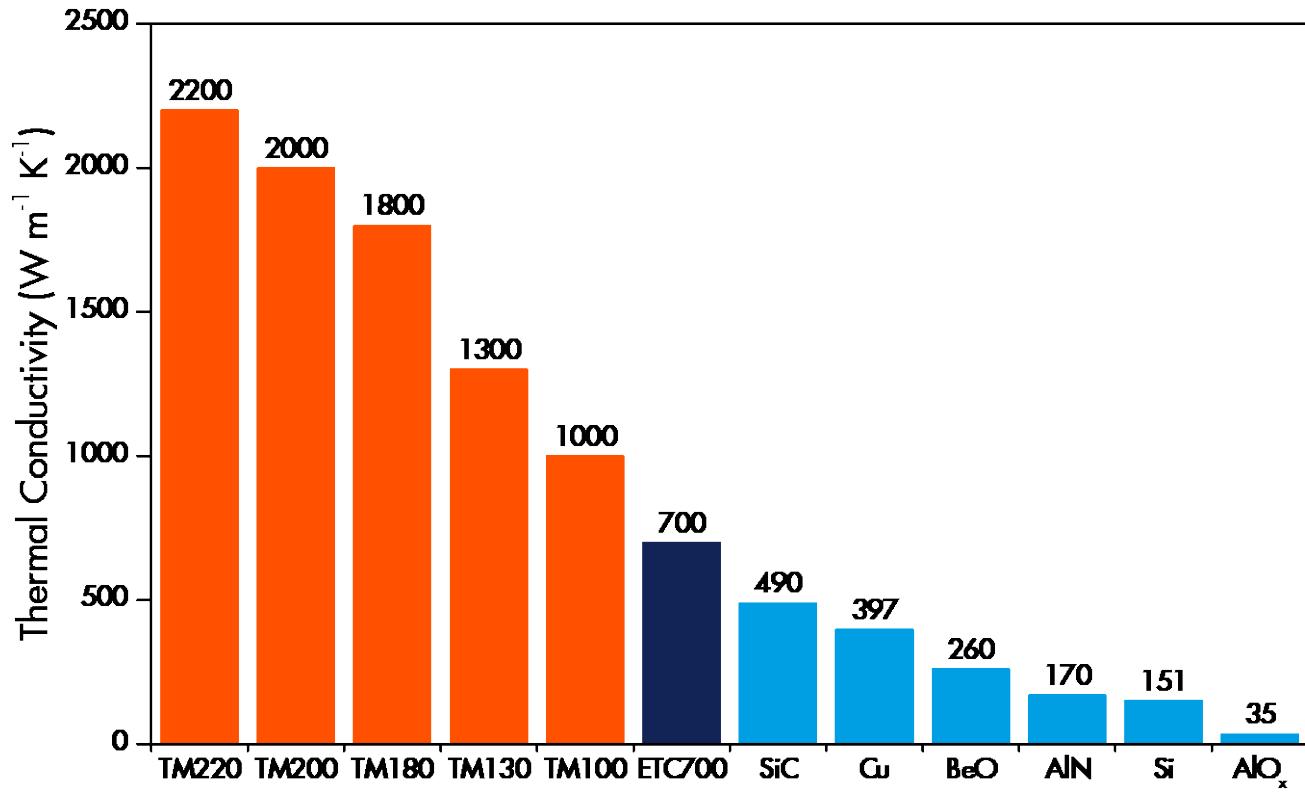
Comparison of model & experimental data



Measured experimental data used to verify the model

Material Grade	Nitrogen (ppm)	Dislocation Density (cm^{-2})	Grain Size (micrometers)	C-Vacancies (ppm)
Optical (711 μm)	0.1-0.4	10^8	120-160	9-13
1800 W/mK (600 μm)	2.0-5.0	10^8	100-140	20-30
1800 W/mK (250 μm)	2.0-5.0	10^8	30-70	20-30
1500 W/mK (250 μm)	12.0-17.0	10^8	30-70	20
1000 W/mK (250 μm)	0.1-0.3	10^{11}	20-30	22-24

CVD diamond heat spreaders



Diameters up to 140 mm & thicknesses of 0.3 to 4 mm

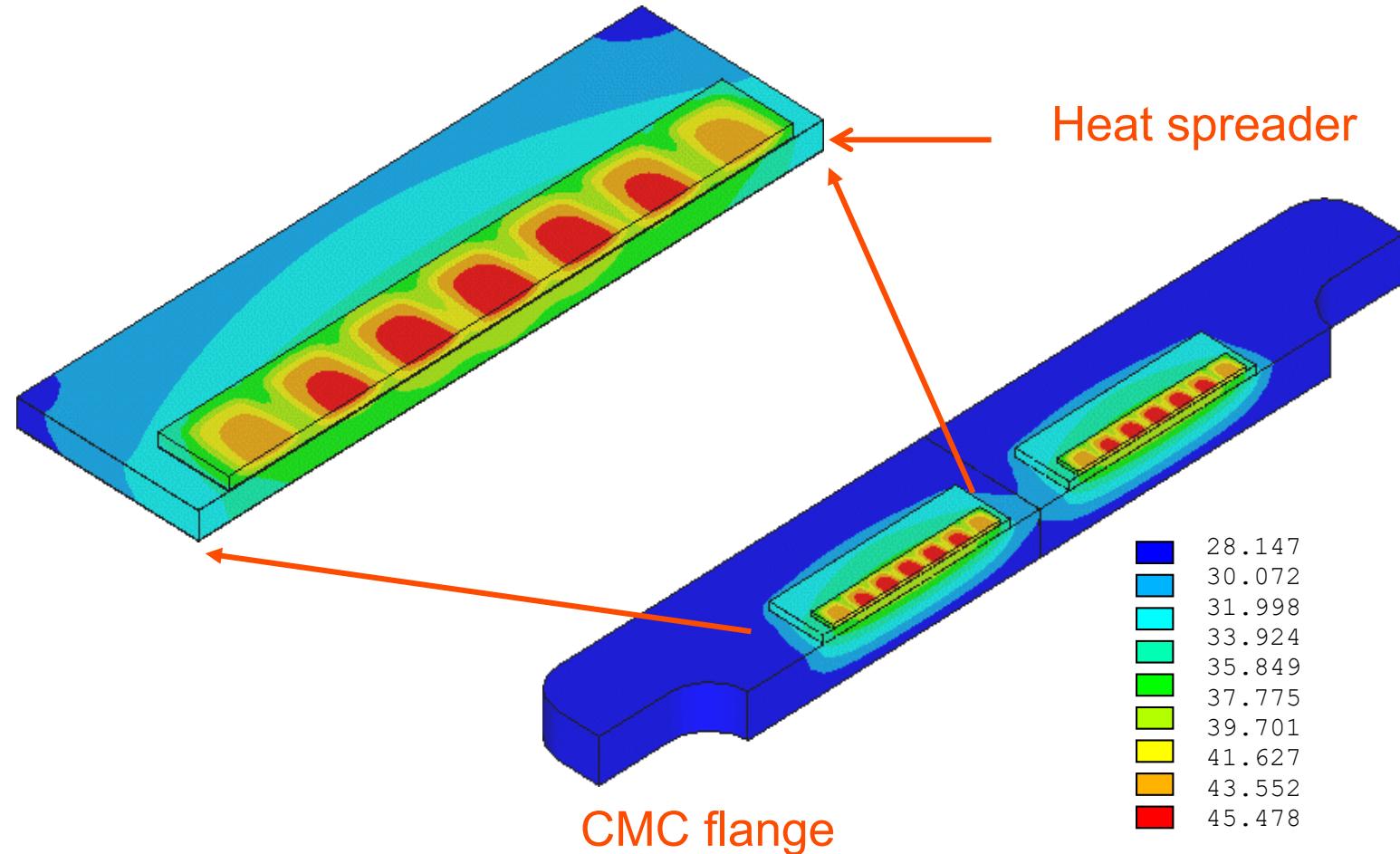
- Controlled synthesis and materials characterization enables different thermal grades
- Thermal conductivity controlled in the range $700 - 2000 \text{ W m}^{-1} \text{K}^{-1}$
- Great than factor 2 thermal conductivity than: GaN:SiC, Cu and Si

The thermal pathway

- Heat spreader characteristics
 - Grade, dimensions TC, CTE
- Heat sink characteristics
 - Material, TC, CTE
- Device characteristics
 - DC, HF, pulsed, continuous
- Attachment method
 - Glues, solder / braze, clamps and pastes
- System requirements
 - Operating temperature

Finite element analysis tools

- Solving the thermal puzzle



Contact us to find out more

E ustechnologies@e6.com
T +1 408 986 2400
W e6.com